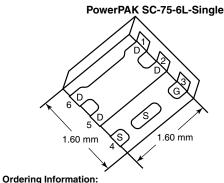


Vishay Siliconix

P-Channel 1.2 V (G-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A) ^g	Q _g (Typ.)						
	0.032 at V _{GS} = - 4.5 V	- 9 ^a							
	0.045 at V _{GS} = - 2.5 V	- 9 ^a							
- 8	0.063 at V _{GS} = - 1.8 V	- 9 ^a	11.3 nC						
	0.120 at V _{GS} = - 1.5 V	- 8.8							
	0.230 at V _{GS} = - 1.2 V	- 6.4							



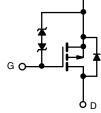
SiB417AEDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

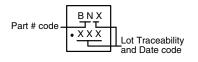
- TrenchFET[®] Power MOSFET
- Thermally Enhanced PowerPAK[®] SC-75 Package
 - Small Footprint Area
 - Low On-Resistance
- 100 % R_g Tested
- Typical ESD Protection 2500 V
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Load Switch for Portable Devices, Smart Phones, and Tablet PCs
 - Low Voltage Drop
 - Space Savings







Marking Code

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	- 8		
Gate-Source Voltage		V _{GS}	± 5	V	
	T _C = 25 °C		- 9 ^a		
Continuous Drain Current (T ₁ = 150 °C)	T _C = 70 °C	I _D	- 9 ^a		
Continuous Drain Current (1) = 150°C)	T _A = 25 °C	טי	- 7.2 ^{b, c}		
	T _A = 70 °C		- 5.7 ^{b, c}	A	
Pulsed Drain Current (t = 300 µs)		I _{DM}	- 15		
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 9 ^a		
Continuous Source-Drain Diode Current	T _A = 25 °C	'S	- 2 ^{b, c}		
	T _C = 25 °C		13		
Maximum Power Dissipation	T _C = 70 °C	P _D	8.4	w	
Maximum Fower Dissipation	T _A = 25 °C	·D	2.4 ^{b, c}	vv	
	T _A = 70 °C		1.6 ^{b, c}		
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 150	<u></u>	
Soldering Recommendations (Peak Temperature	e) ^{d, e}		260		

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	$ \text{ um Junction-to-Ambient}^{\text{b, f}} \qquad \qquad t \leq 5 \text{ s} $		41	51	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	7.5	9.5	0/11				

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 105 °C/W.

g. Based on $T_C = 25$ °C.



COMPLIANT HALOGEN

FREE

o s

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static									
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_{D} = -250 \mu A$	- 8			V			
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μΑ		- 6.1		mV/°C			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_{\rm D} = -250 \mu {\rm A}$		2.1					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.35		- 1	V			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 5 V$			± 20	μΑ			
Zava Oata Maltana Duain Ouwant		$V_{DS} = -8 V, V_{GS} = 0 V$			- 1				
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -8 V, V_{GS} = 0 V, T_{J} = 55 °C$			- 10				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 5 V, V_{GS} = - 4.5 V	- 15			Α			
		V _{GS} = - 4.5 V, I _D = - 3 A		0.0265	0.0320)			
		V _{GS} = - 2.5 V, I _D = - 3 A		0.0360	0.0450	Ω			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 1.8 V, I _D = - 1 A		0.0500	0.0630				
	- (-)	V _{GS} = - 1.5 V, I _D = - 0.5 A		0.0600	0.1200	1			
		$V_{GS} = -1.2 \text{ V}, I_D = -0.5 \text{ A}$		0.1000	0.2300	-			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 4 V, I _D = - 7.4 A		18		S			
Dynamic ^b	010				L				
Input Capacitance									
Output Capacitance	C _{oss}	V _{DS} = - 4 V, V _{GS} = 0 V, f = 1 MHz		878 415		pF			
Reverse Transfer Capacitance	C _{rss}			735					
-		V _{DS} = - 4 V, V _{GS} = - 5 V, I _D = - 7.4 A		12.3	18.5	nC			
Total Gate Charge	Qg			11.3	17				
Gate-Source Charge	Q _{gs}	V _{DS} = - 4 V, V _{GS} = - 4.5 V, I _D = - 7.4 A		1.35					
Gate-Drain Charge	Q _{gd}			3.42					
Gate Resistance	R _q	f = 1 MHz	1.3	6.5	13	Ω			
Turn-On Delay Time	t _{d(on)}			19	29				
Rise Time	t_r $V_{DD} = -4 V, R_1 = 0.68 \Omega$			18	27				
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -5.9 \text{ A}, \text{ V}_{\text{GEN}} = -4.5 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		32	48	ns			
Fall Time	t _f			19	29	1			
Drain-Source Body Diode Characteris	tics					1			
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			- 9				
Pulse Diode Forward Current	I _{SM}	-			- 15	A			
Body Diode Voltage	V _{SD}	I _S = - 5.9 A, V _{GS} = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time				32	48	ns			
Body Diode Reverse Recovery Charge	Q _{rr}			13	20	nC			
Reverse Recovery Fall Time	ta	I _F = - 5.9 A, dl/dt = 100 A/μs, T _J = 25 °C		14	-				
						ns			

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

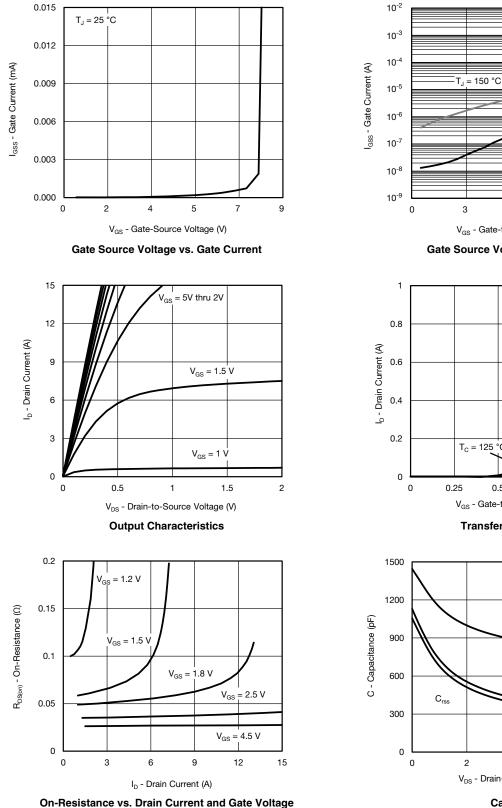
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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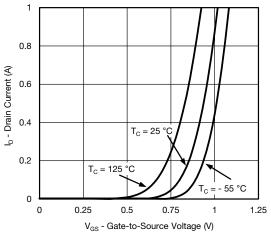
SiB417AEDK Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

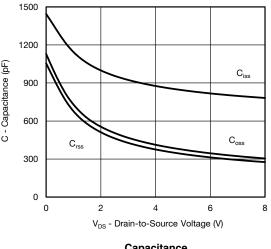


T_{.1} = 25 °C 6 9 12 V_{GS} - Gate-to-Source Voltage (V)

Gate Source Voltage vs. Gate Current



Transfer Characteristics

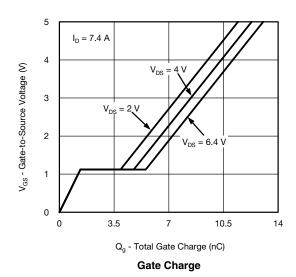


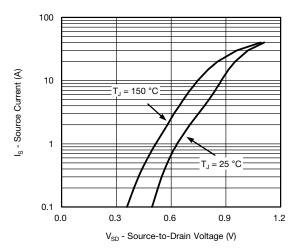
Capacitance



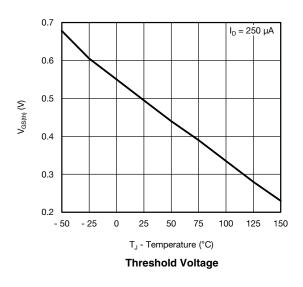
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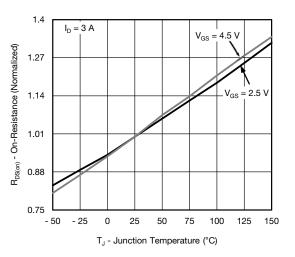
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



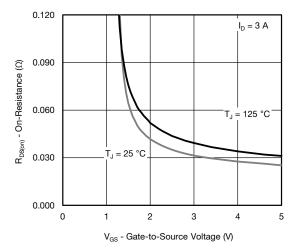


Soure-Drain Diode Forward Voltage

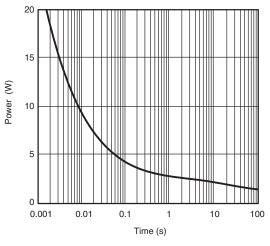




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



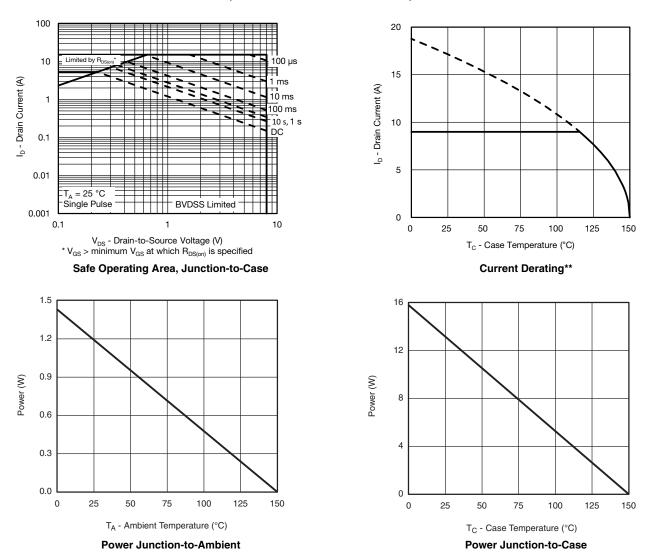
Single Pulse Power, Junction-to-Ambient

For technical questions, contact: pmostechsupport@vishay.com

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SiB417AEDK Vishay Siliconix



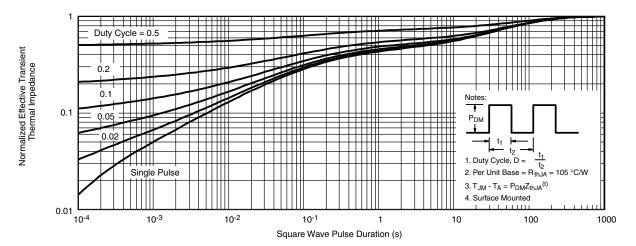
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

** The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

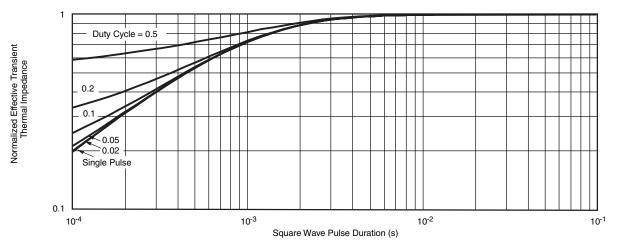


Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63899.

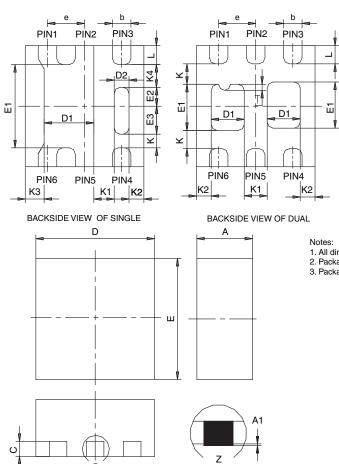
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Package Information

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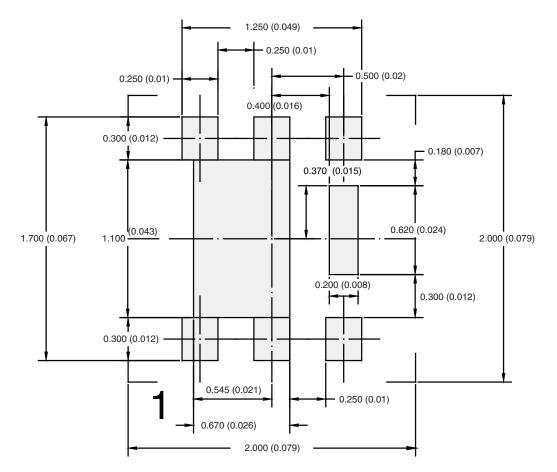
- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

DETAIL Z

		SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021	
D2	0.10	0.20	0.30	0.004	0.008	0.012							
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028	
E2	0.20	0.25	0.30	0.008	0.010	0.012							
E3	0.32	0.37	0.42	0.013	0.015	0.017							
е		0.50 BSC			0.020 BSC		0.50 BSC			0.020 BSC			
К		0.180 TYP 0.007 TYP				0.245 TYP			0.010 TYP				
K1		0.275 TYP			0.011 TYP		0.320 TYP			0.013 TYP			
K2	0.200 TYP			0.008 TYP			0.200 BSC		0.008 TYP				
K3	0.255 TYP			0.010 TYP									
K4	0.300 TYP			0.012 TYP									
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014	
Т							0.03	0.08	0.13	0.001	0.003	0.005	
	ECN: C-07431 – Rev. C, 06-Aug-07 DWG: 5935												



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC75-6L Single



Dimensions in mm/(Inches)

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